

October 2013

# **FCB20N60**

# N-Channel SuperFET<sup>®</sup> MOSFET 600 V, 20 A, 190 mΩ

#### **Features**

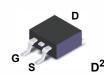
- 650 V @T<sub>.1</sub> = 150 °C
- Typ.  $R_{DS(on)}$  = 150 m $\Omega$
- Ultra Low Gate Charge (Typ. Q<sub>q</sub> = 75 nC)
- Low Effective Output Capacitance (Typ. C<sub>oss</sub>.eff = 165 pF)
- 100% Avalanche Tested
- · RoHS Compliant

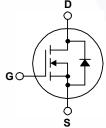
# **Application**

- · Lighting
- · AC-DC Power Supply
- · Solar Inverter

# Description

SuperFET® MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low onresistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.





# MOSFET Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol		Parameter		FCB20N60TM	Unit
V <sub>DSS</sub>	Drain to Source Voltage			600	V
	Drain Current	- Continuous (T <sub>C</sub> = 25°C)		20	^
ID	Drain Current	- Continuous (T <sub>C</sub> = 100°C)		12.5	_ A
I <sub>DM</sub>	Drain Current	- Pulsed (No	te 1)	60.0	Α
V <sub>GSS</sub>	Gate to Source Voltage			±30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)		te 2)	690	mJ
I <sub>AR</sub>	Avalanche Current (Not		te 1)	20	Α
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1		te 1)	20.8	mJ
dv/dt	Peak Diode Recovery dv/	'dt (No	te 3)	4.5	V/ns
D	Dawar Dissination	(T <sub>C</sub> = 25°C)		208	W
$P_{D}$	Power Dissipation	- Derate above 25°C		1.67	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300	°C

## **Thermal Characteristics**

Symbol	Parameter	FCB20N60TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.6	
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (1 in <sup>2</sup> pad of 2 oz copper), Max.	40	

# **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FCB20N60	FCB20N60TM	D <sup>2</sup> -PAK	330mm	24m	800

# **Electrical Characteristics** $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
D\/	Drain to Source Proakdown Voltage	$V_{GS} = 0 \text{ V,I}_{D} = 250 \mu\text{A}, \text{ T}_{C} = 25^{\circ}\text{C}$	600	-	-	V
BV <sub>DSS</sub> Drain to Source Breakdown Voltage	Drain to Source Breakdown voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}, T_C = 150^{\circ}\text{C}$	-	650	-	V
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C	-	0.6	-	V/°C
BV <sub>DS</sub>	Drain-Source Avalanche Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 20 A	-	700	-	V
	Zoro Cato Voltago Proin Current	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	-	-	1	
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μА
I <sub>GSS</sub>	Gate to Body Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±100	nA

### **On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	3.0	-	5.0	V
R <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	0.15	0.19	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40 V, I <sub>D</sub> = 10 A	-	17	-	S

# **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V - 25 V V - 0 V	- \	2370	3080	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V f = 1.0 MHz		1280	1665	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			95	-	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 480 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$	-	65	85	pF
C <sub>oss</sub> eff.	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 400 \text{ V}, V_{GS} = 0 \text{ V}$	-	165	-	pF

# **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		-	62	135	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{DD} = 300 \text{ V}, I_{D} = 20 \text{ A}$ $R_{G} = 25 \Omega$		140	290	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			230	470	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4	-	65	140	ns
Q <sub>g(tot)</sub>	Total Gate Charge at 10V	V <sub>DS</sub> = 480 V, I <sub>D</sub> = 20 A,	/-	75	98	nC
$Q_{gs}$	Gate to Source Gate Charge	V <sub>GS</sub> = 10 V	-	13.5	18	nC
$Q_{gd}$	Gate to Drain "Miller" Charge	(Note 4	_	36	-	nC

# **Drain-Source Diode Characteristics**

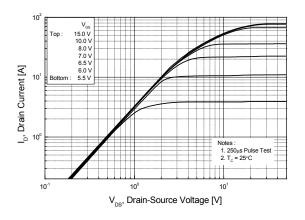
I <sub>S</sub>	Maximum Continuous Drain to Source Dioc	Maximum Continuous Drain to Source Diode Forward Current			20	Α
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current			-	60	Α
$V_{SD}$	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 20 A	-	-	1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 20 A	-	530	//-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{GS} = 0 \text{ V, } I_{SD} = 20 \text{ A}$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$	-	10.5	-	μС

#### Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.  $I_{AS}$  = 10 A,  $V_{DD}$  = 50 V,  $R_G$  = 25  $\Omega$ , Starting  $T_J$  = 25°C
- 3. I  $_{SD} \leq~20$  A, di/dt  $\leq 200$  A/µs, V  $_{DD} \leq BV _{DSS}$ , Starting T  $_{J}$  =  $25^{\circ}C$
- 4. Essentially Independent of Operating Temperature Typical Characteristics

# **Typical Performance Characteristics**

Figure 1. On-Region Characteristics



**Figure 2. Transfer Characteristics** 

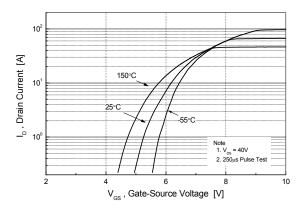


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

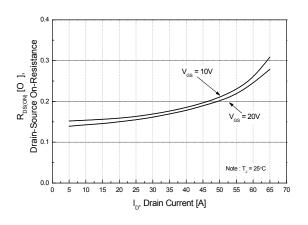


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

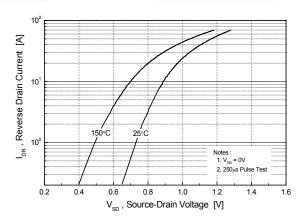


Figure 5. Capacitance Characteristics

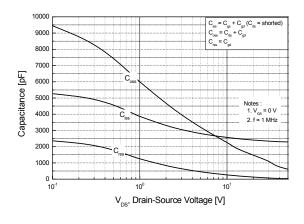
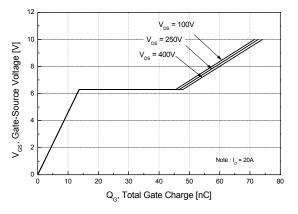


Figure 6. Gate Charge Characteristics



# Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

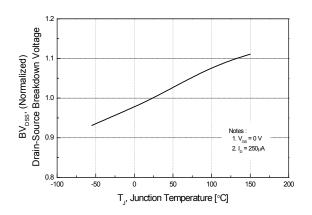


Figure 8. On-Resistance Variation vs. Temperature

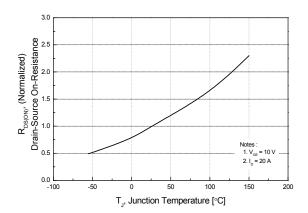


Figure 9. Maximum Safe Operating Area

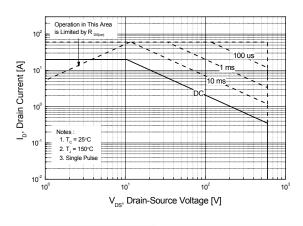


Figure 10. Maximum Drain Current vs. Case Temperature

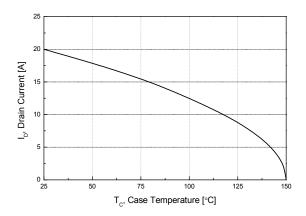


Figure 11. Transient Thermal Response Curve

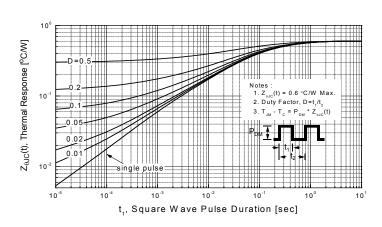


Figure 12. Gate Charge Test Circuit & Waveform

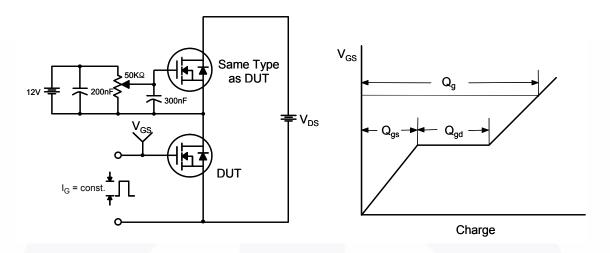


Figure 13. Resistive Switching Test Circuit & Waveforms

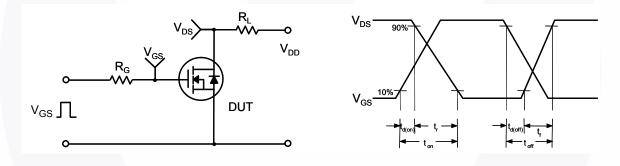
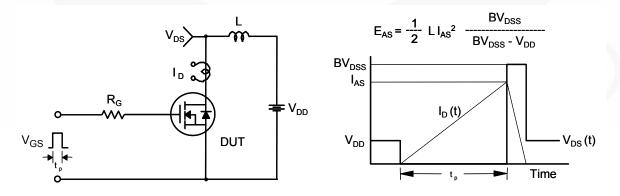


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



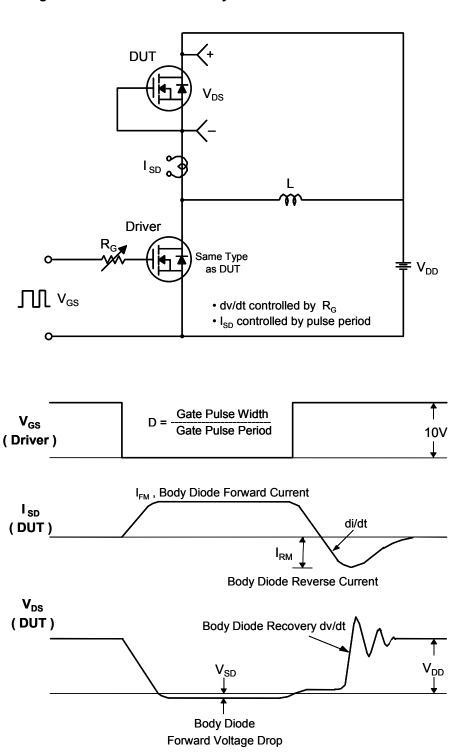


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

# **Mechanical Dimensions**

# TO-263 2L (D<sup>2</sup>PAK)

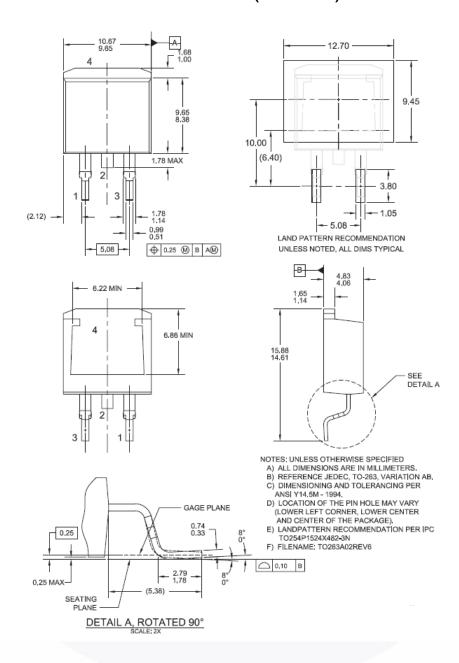


Figure 16. 2LD, TO263, Surface Mount

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Dimension in Millimeters





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